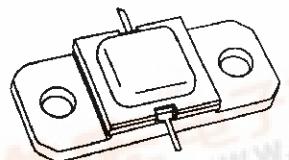



AM80610-030
**RF & MICROWAVE TRANSISTORS
UHF COMMUNICATIONS APPLICATIONS**

- REFRACTORY/GOLD METALLIZATION
- Emitter SITE BALLASTED
- INPUT/OUTPUT MATCHING
- METAL/CERAMIC HERMETIC PACKAGE
- $P_{OUT} = 30 \text{ W MIN. WITH } 8.5 \text{ dB GAIN}$



.400 x .400 2NLFL (S042)
hermetically sealed

ORDER CODE
AM80610-030

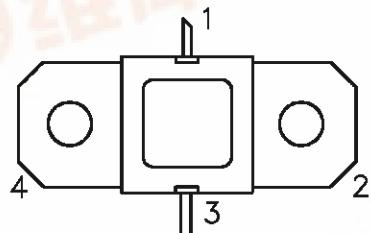
BRANDING
80610-30

DESCRIPTION

The AM80610-030 is a high power, common base NPN silicon bipolar device optimized for CW operation in the 620 - 960 MHz frequency range.

AM80610-030 utilizes a rugged, overlay, emitter-ballasted L-Band die geometry to achieve high gain and collector efficiency and is suitable for driver or output stage use in Class C power amplifiers. Typical applications include military communications, ECM, and test equipment.

The AM80610-030 is provided in the industry-standard, metal/ceramic AMPAC™ hermetic package.

PIN CONNECTION


1. Collector 3. Emitter
2. Base 4. Base

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
P _{DISS}	Power Dissipation* (T _C ≤ 50°C)	57	W
I _C	Device Current*	3.0	A
V _{CC}	Collector-Supply Voltage*	32	V
T _J	Junction Temperature	200	°C
T _{STG}	Storage Temperature	– 65 to +200	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance*	2.6	°C/W
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ELECTRICAL SPECIFICATIONS ($T_{case} = 25^\circ\text{C}$)

STATIC

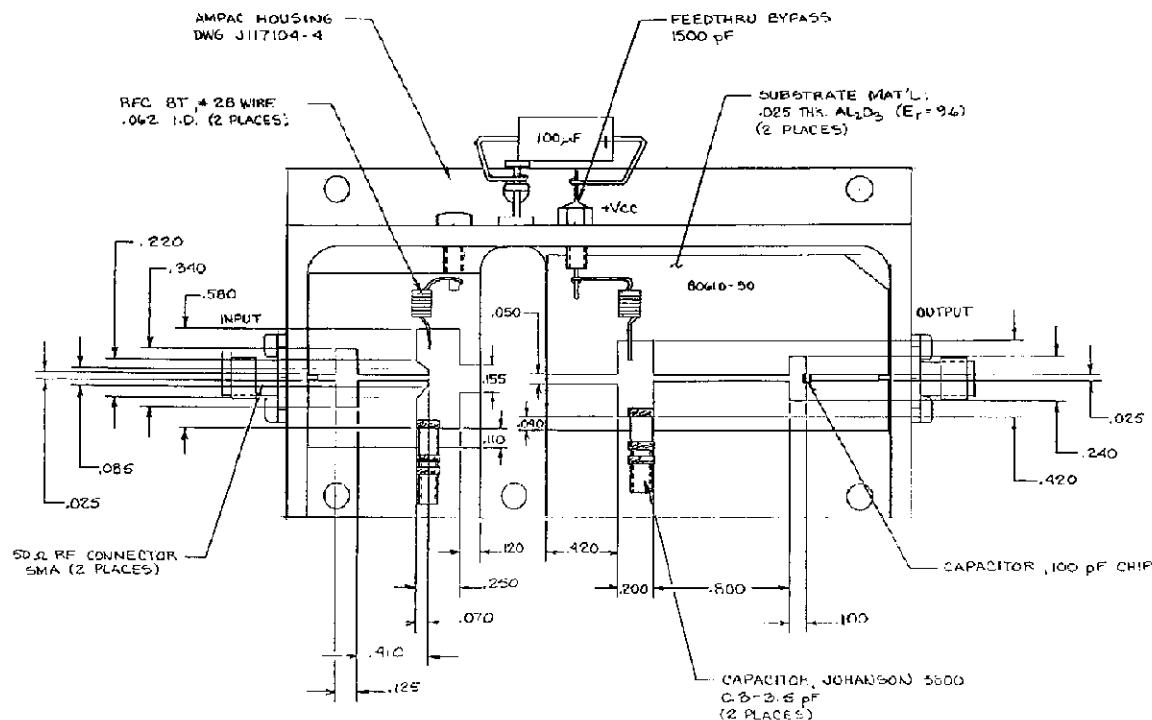
Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV_{CBO}	$I_C = 20 \text{ mA}$	55	—	—	V
BV_{EBO}	$I_E = 2 \text{ mA}$	3.5	—	—	V
BV_{CER}	$I_C = 40 \text{ mA}$	55	—	—	V
I_{CES}	$V_{BE} = 0 \text{ V}$	—	—	10	mA
h_{FE}	$V_{CE} = 5 \text{ V}$	15	—	150	—

DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 620 – 960 MHz	P _{IN} = 4.2 W	V _{CC} = 28 V	30	—	—	W
η _C	f = 620 – 960 MHz	P _{IN} = 4.2 W	V _{CC} = 28 V	50	—	—	%
G _P	f = 620 – 960 MHz	P _{IN} = 4.2 W	V _{CC} = 28 V	8.5	—	—	dB

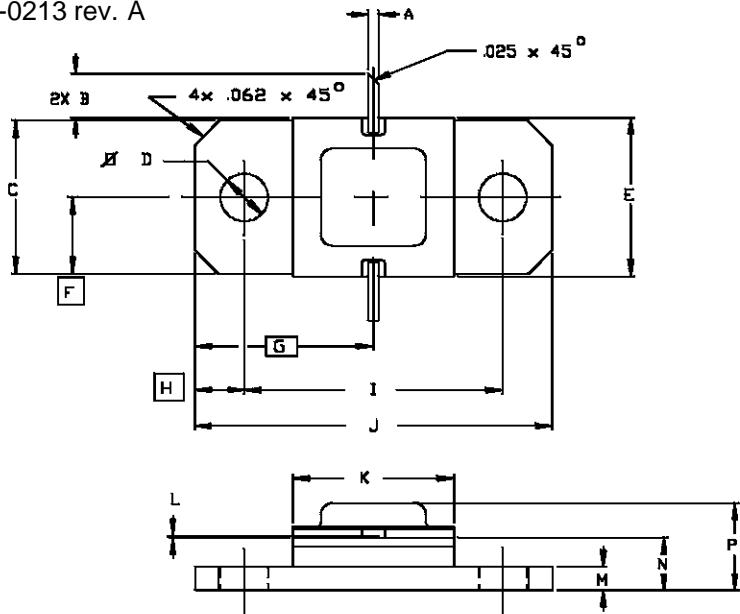
TEST CIRCUIT

Dwg.No. C127464



PACKAGE MECHANICAL DATA

Ref.: Dwg. No. 12-0213 rev. A



SGS-THOMSON MICROELECTRONICS		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.020/.51	.030/.76
B	.100/2.54	
C	.376/9.55	.396/10.06
D	.110/2.79	.130/3.30
E	.395/10.03	.407/10.34
F	.193/4.90	
G	.450/11.43	
H	.125/3.18	
I	.640/16.26	.660/16.76
J	.890/22.61	.910/23.11

CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
K	.395/10.03	.415/10.54
L	.004/0.10	.006/0.16
M	.052/1.32	.072/1.83
N	.118/3.00	.131/3.33
P		.230/5.84